



REV 09/01

Features

Top-illuminated InGaAs/InP pin photodiode High speed response: t_{FWHM} 14 ps On chip coplanar waveguide (Z = 50 Ω) Diameter of light sensitive area 30 μ m Wire bondable or flip-chip solderable High responsivity from 800 to 1600 nm

Product Description

The PDCS30T is an InGaAs/InP very high speed photodiode chip with a tapered coplanar transmission line. The top-illuminated p-i-n photodiode structure offers excellent responsivity and high speed of response for the wavelength region 800 to 1600 nm. The photodiode, which achieves full speed already at 1.5 volt bias, is intended for use in high-speed receiver front-ends and for optical measurement equipment with picosecond time resolution.

Specifications @ T=25°C

Parameter		Sym	Min	Тур	Max	Unit
Responsivity	λ = 1550 nm	R		0.8		A/W
	λ = 1300 nm			0.9		
Optical pulse energy		Εp			50	fJ
CW optical power		Pcw			3	dBm
Bias voltage		V+		2.0		V
Dark current	V _r = 2.5 V	ΙD		5		nA
Bandwidth		В		14		GHz
Optical pulse response		t _{FWHM}	•	28	¬	ps



